

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- High Current Density Enhanced DMOS SPT
- Isolated AISiC Base With AlN Substrates

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives
- Choppers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM500GCM33-TS000 is a 3300V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) chopper module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM500GCM33-TS000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	3300V
$V_{CE(sat)}$ * (typ)	2.2V
I_C (max)	500A
$I_{C(PK)}$ (max)	1000A

* Measured at the auxiliary terminals

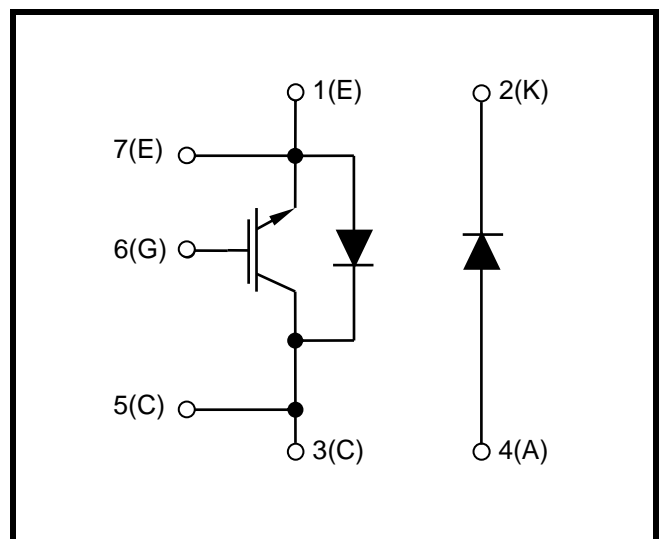


Fig. 1 Circuit configuration



Outline type code: G

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0\text{V}$	3300	V
V_{GES}	Gate-emitter voltage		± 20	V
I_C	Continuous collector current	$T_{case} = 110^{\circ}\text{C}$	500	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 140^{\circ}\text{C}$	1000	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	5.2	kW
I^2t	Diode I^2t value (IGBT arm)	$V_R = 0$, $t_p = 10\text{ms}$, $T_j = 125^{\circ}\text{C}$	80	kA^2s
	Diode I^2t value (Diode arm)		80	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q_{PD}	Partial discharge – per module	IEC1287, $V_1 = 3500\text{V}$, $V_2 = 2600\text{V}$, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor (per arm)	Continuous dissipation – junction to case	-	-	24	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance – diode (IGBT arm)	Continuous dissipation – junction to case			48	$^{\circ}\text{C}/\text{kW}$
	Thermal resistance – diode (Diode arm)				48	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	150	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS
T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = V _{CES}			2	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125°C			30	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 150°C			50	mA
I _{GES}	Gate leakage current	V _{GE} = ± 20V, V _{CE} = 0V			1	µA
V _{GE(TH)}	Gate threshold voltage	I _C = 40mA, V _{GE} = V _{CE}		5.7		V
V _{CE(sat)}	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 500A		2.2		V
		V _{GE} = 15V, I _C = 500A, T _j = 125°C		2.8		V
		V _{GE} = 15V, I _C = 500A, T _j = 150°C		3.0		V
I _F	Diode forward current	DC		500		A
I _{FM}	Diode maximum forward current	t _p = 1ms		1000		A
V _F [†]	Diode forward voltage (IGBT arm)	I _F = 500A		2.4		V
	Diode forward voltage (Diode arm)			2.4		V
	Diode forward voltage (IGBT arm)	I _F = 500A, T _j = 125°C		2.5		V
	Diode forward voltage (Diode arm)			2.5		V
	Diode forward voltage (IGBT arm)	I _F = 500A, T _j = 150°C		2.4		V
	Diode forward voltage (Diode arm)			2.4		V
C _{ies}	Input capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		90		nF
Q _g	Gate charge	±15V		10		µC
C _{res}	Reverse transfer capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		2		nF
L _M	Module inductance – per arm			25		nH
R _{INT}	Internal resistance – per arm			260		µΩ
SC _{Data}	Short circuit current, I _{SC}	T _j = 150°C, V _{CC} = 2500V t _p ≤ 10µs, V _{GE} ≤ 15V V _{CE(max)} = V _{CES} - L* x di/dt IEC 60747-9		1850		A

Note:
[†] Measured at the power busbars, not the auxiliary terminals

^{*} L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

 $T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 500\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{G(\text{ON})} = 4.7\Omega$ $R_{G(\text{OFF})} = 4.7\Omega$ $C_{ge} = 100\text{nF}$ $L_S \sim 100\text{nH}$		2700		ns	
t_f	Fall time			520		ns	
E_{OFF}	Turn-off energy loss				1000		mJ
$t_{d(\text{on})}$	Turn-on delay time				1000		ns
t_r	Rise time				400		ns
E_{ON}	Turn-on energy loss				650		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 500\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 1400\text{A}/\mu\text{s}$		285		μC	
I_{rr}	Diode reverse recovery current			310		A	
E_{rec}	Diode reverse recovery energy			350		mJ	

 $T_{\text{case}} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 500\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{G(\text{ON})} = 4.7\Omega$ $R_{G(\text{OFF})} = 4.7\Omega$ $C_{ge} = 100\text{nF}$ $L_S \sim 100\text{nH}$		2750		ns	
t_f	Fall time			570		ns	
E_{OFF}	Turn-off energy loss				1100		mJ
$t_{d(\text{on})}$	Turn-on delay time				1020		ns
t_r	Rise time				420		ns
E_{ON}	Turn-on energy loss				850		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 500\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 1400\text{A}/\mu\text{s}$		470		μC	
I_{rr}	Diode reverse recovery current			390		A	
E_{rec}	Diode reverse recovery energy			600		mJ	

 $T_{\text{case}} = 150^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 500\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{G(\text{ON})} = 4.7\Omega$ $R_{G(\text{OFF})} = 4.7\Omega$ $C_{ge} = 100\text{nF}$ $L_S \sim 100\text{nH}$		2800		ns	
t_f	Fall time			550		ns	
E_{OFF}	Turn-off energy loss				1150		mJ
$t_{d(\text{on})}$	Turn-on delay time				1030		ns
t_r	Rise time				430		ns
E_{ON}	Turn-on energy loss				950		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 500\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 1400\text{A}/\mu\text{s}$		535		μC	
I_{rr}	Diode reverse recovery current			400		A	
E_{rec}	Diode reverse recovery energy			650		mJ	

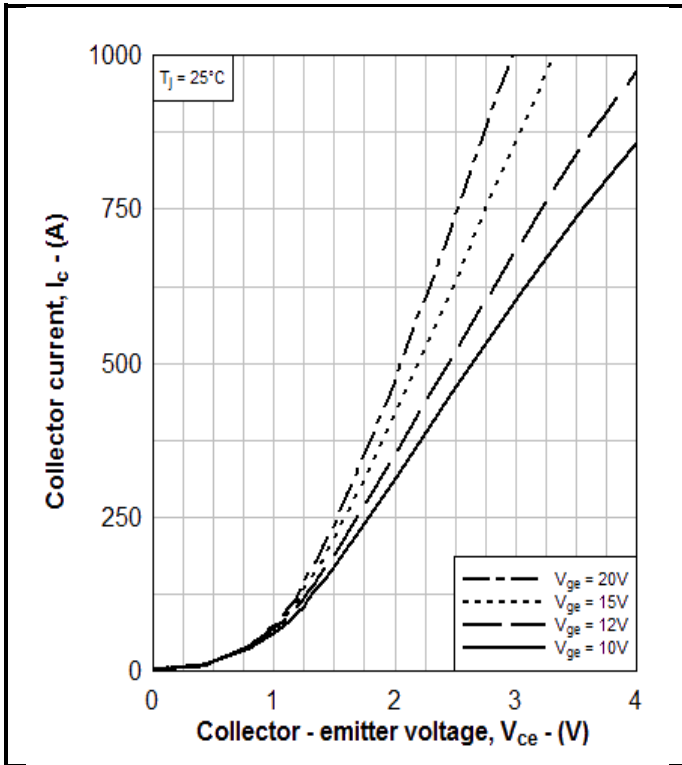


Fig. 3 Typical output characteristics

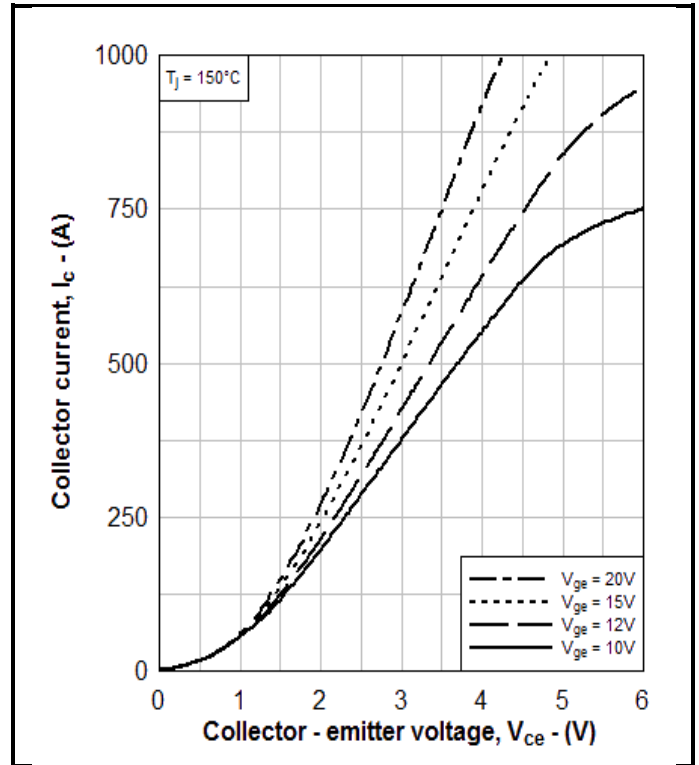


Fig. 4 Typical output characteristics

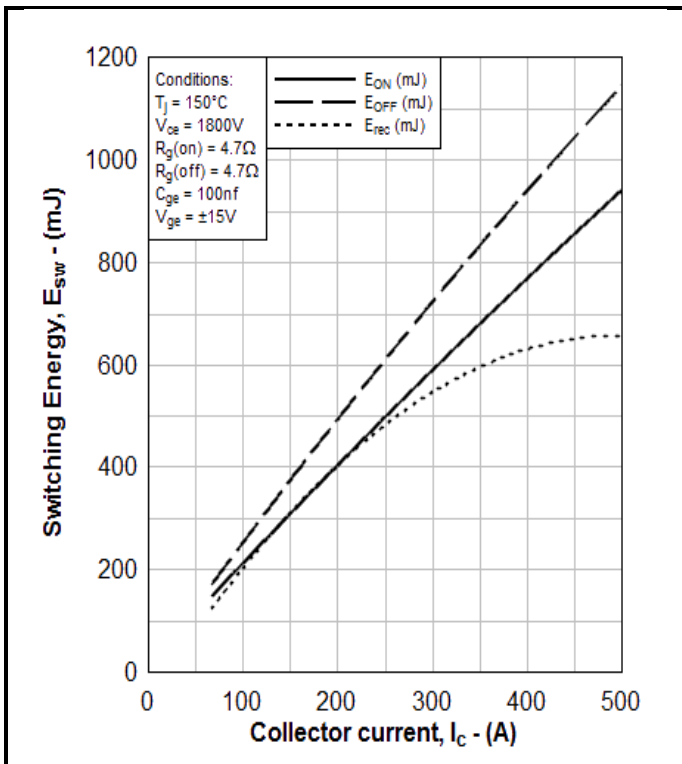


Fig. 5 Typical switching energy vs collector current

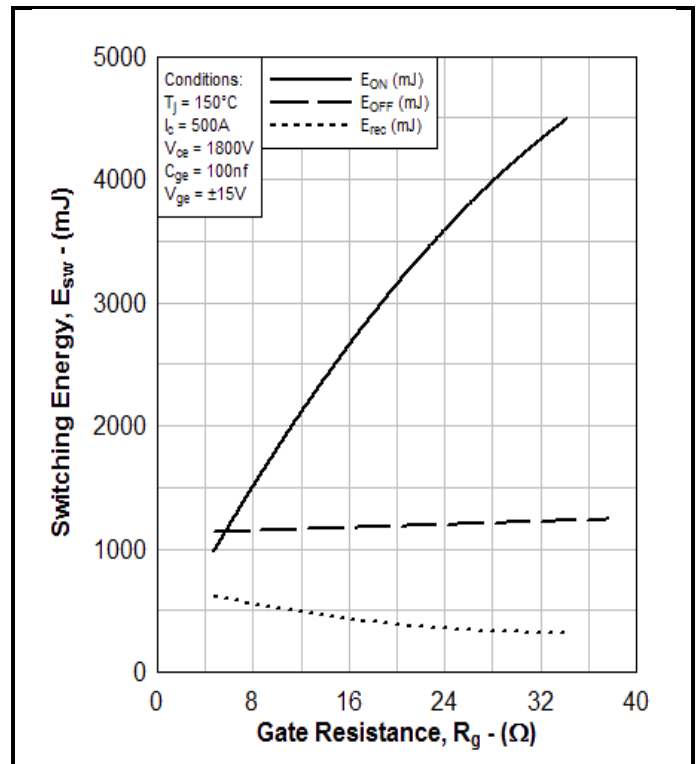


Fig. 6 Typical switching energy vs gate resistance

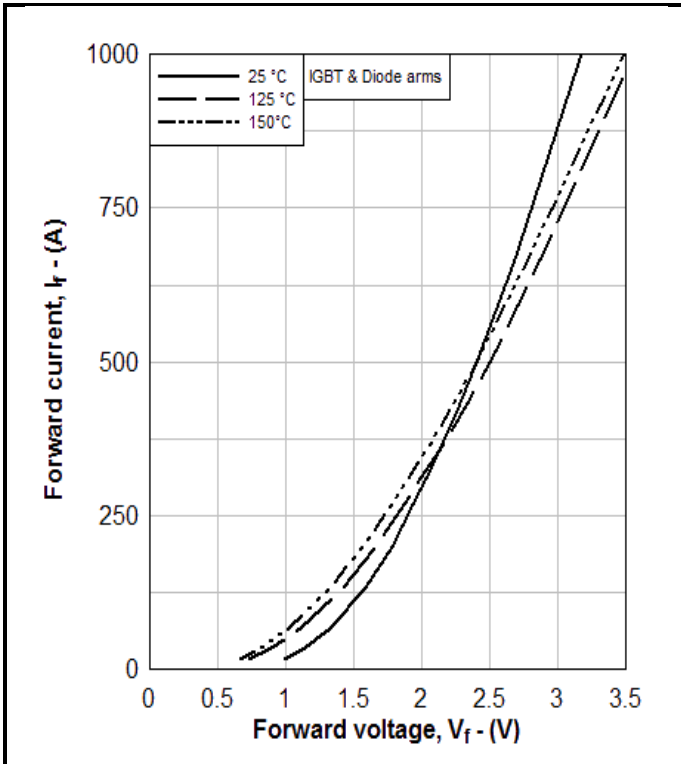


Fig. 7 Diode typical forward characteristics

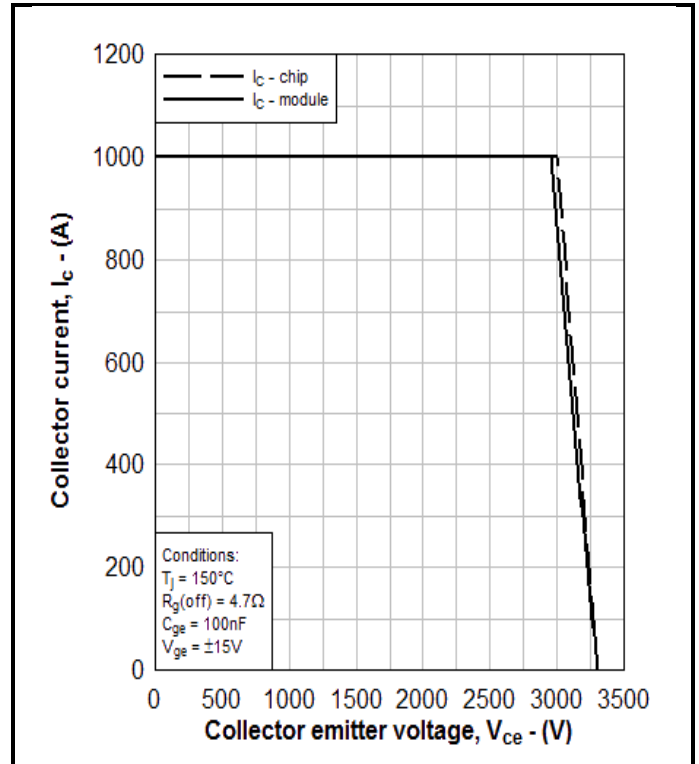


Fig. 8 Reverse bias safe operating area

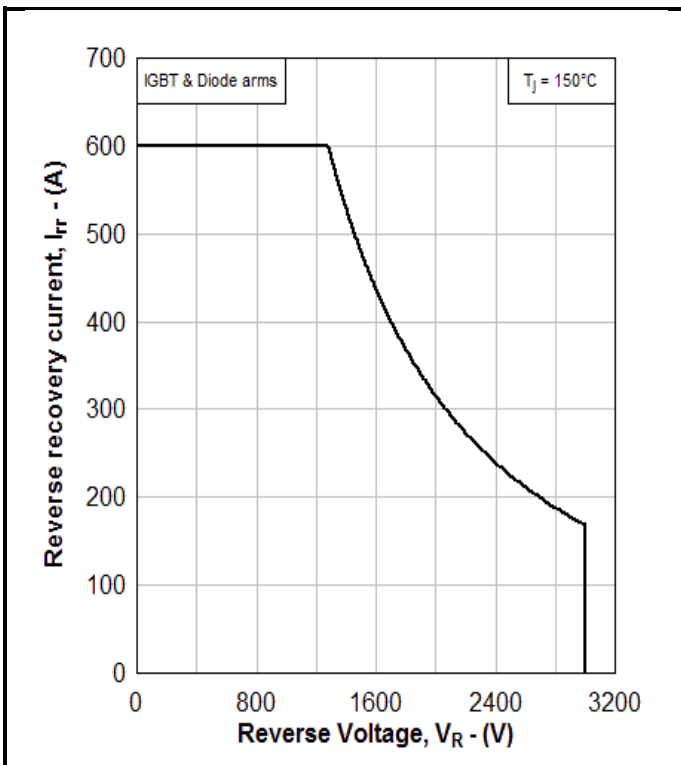


Fig. 9 Diode reverse bias safe operating area

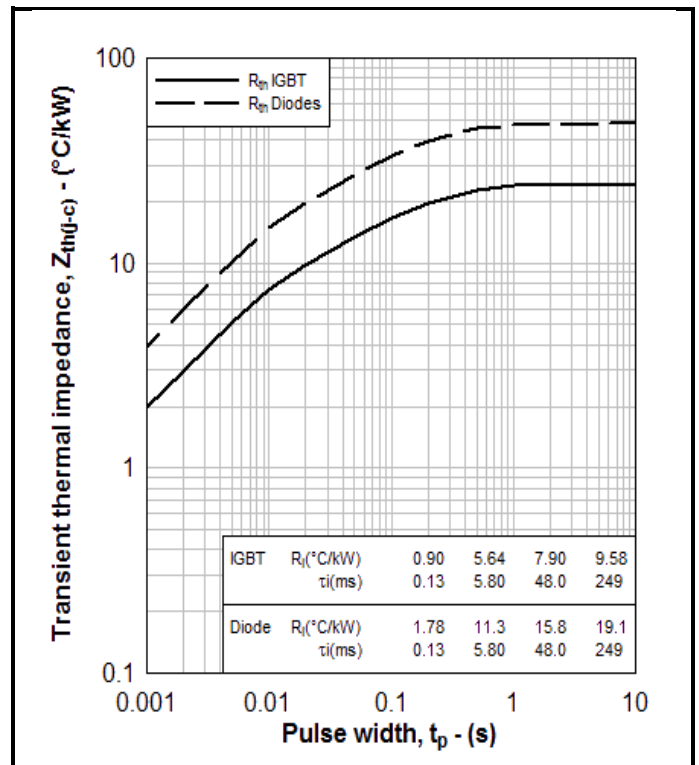
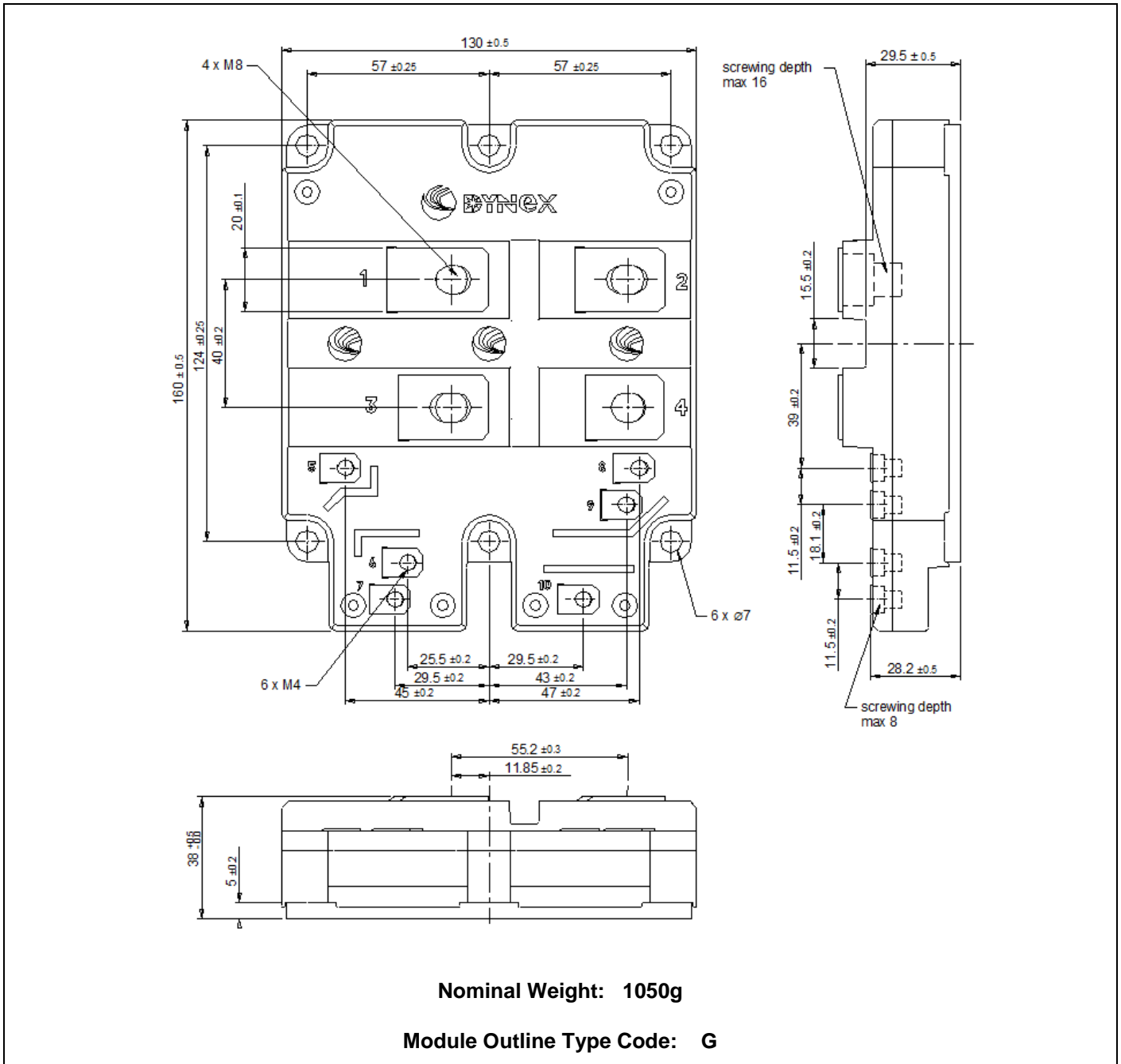


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
 All dimensions in mm, unless stated otherwise.
DO NOT SCALE.


Fig. 11 Module outline drawing

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